

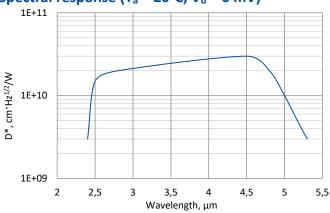
# PVI-5-1×1-TO39-NW-36

# 2.4 – 5.5 μm HgCdTe ambient temperature, optically immersed photovoltaic

# detector

**PVI-5-1×1-T039-NW-36** is uncooled IR photovoltaic detector based on sophisticated HgCdTe heterostructure for the best performance and stability. The device is optimized for the maximum performance at 5  $\mu$ m. Detector element is monolithically integrated with hyperhemispherical GaAs microlens in order to improve performance of the device. Reverse bias may significantly increase response speed and dynamic range. It also results in improved performance at high frequencies, but 1/f noise that appears in biased devices may reduce performance at low frequencies

#### Spectral response ( $T_a = 20$ °C, $V_b = 0$ mV)





Exemplary spectral detectivity, the spectral response of delivered devices may differ.

### Specification ( $T_a = 20$ °C, $V_b = 0$ mV)

Parameter	Detector type
	PVI-5-1x1-TO39-NW-36
Active element material	epitaxial HgCdTe heterostructure
Cut-on wavelength $\lambda_{\text{cut-on}}$ (10%), $\mu$ m	2.4±0.5
Peak wavelength λ <sub>peak</sub> , μm	4.2±0.5
Optimum wavelength λ <sub>opt</sub> , μm	5.0
Cut-off wavelength $\lambda_{\text{cut-off}}$ (10%), $\mu$ m	5.5±0.3
Detectivity D*( $\lambda_{peak}$ ), cm·Hz <sup>1/2</sup> /W	≥3.0×10 <sup>10</sup>
Detectivity D*( $\lambda_{opt}$ ), cm·Hz <sup>1/2</sup> /W	≥1.0×10 <sup>10</sup>
Current responsivity R <sub>i</sub> (λ <sub>peak</sub> ), A/W	≥2.0
Current responsivity $R_i(\lambda_{opt})$ , A/W	≥1.0
Time constant τ, ns	≤150
Resistance R, $\Omega$	≥100
Optical area Ao, mm×mm	1×1
Package	TO39
Acceptance angle Φ	~36°
Window	none

#### **Features**

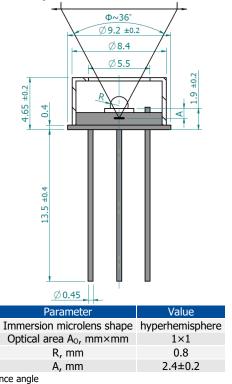
- Wide dynamic range
- Convenient to use
- Very small size
- Cost-effective solution
- Quantity discounted price
- Fast delivery

#### **Applications**

- Contactless temperature measurements (railway transport, industrial and laboratory processes monitoring)
- Flame and explosion detection
- Threat warning systems
- Gas detection, monitoring and analysis (CO, CO<sub>2</sub>, NO<sub>x</sub>)
- Breath analysis
- Solids analysis
- Leakage control in gas pipelines
- Combustion process control

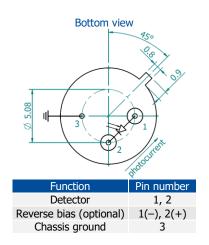








R – hyperhemisphere microlens radius A – distance from the bottom of hyperhemisphere microlens to the focal plane



#### Precautions for use and storage

- Standard ohmmeter may overbias and damage the detector. Bias of 10 mV can be used for resistance measurements.
- Operation in 10% to 80% humidity and -20°C to 30°C ambient temperature.
- Beam power limitations for optically immersed detector:
  - irradiance with CW or single pulse longer than 1 µs irradiance on the apparent optical active area must not exceed
  - irradiance of the pulse shorter than 1 µs must not exceed 10 kW/cm<sup>2</sup>.
- Storage in dark place with 10% to 90% humidity and -20°C to 50°C ambient temperature.

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